# FAIRCHILD™

Is Now Part of

ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at
www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

FAIRCHILD
SEMICONDUCTOR TM

KSD1691

Feature

- Low Collector-Emtter Saturation Voltage & Large Collector Current
- High Power Dissipation: P_C = 1.3W (T_a=25°C)
- Complementary to KSB1151

1
TO-126
1. Emitter   2.Collector   3.Base
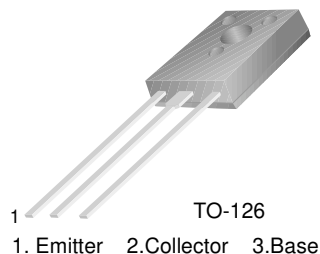
NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current (DC)	5	A
I_{CP}	*Collector Current (Pulse)	8	A
I_B	Base Current (DC)	1	A
P_C	Collector Dissipation (T_a=25°C)	1.3	W
P_C	Collector Dissipation (T_C=25°C)	20	W
T_J	Junction Temperature	150	°C
T_{STG}	Storage Temperature	- 55 ~ 150	°C

* PW≤10ms, duty Cycle≤50%

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
I_{CBO}	Collector Cut-off Current	V_{CB} = 50V, I_E = 0			10	μA
I_{EBO}	Emitter Cut-off Current	V_{EB} = 7V, I_C = 0			10	μA
h_{FE1} h_{FE2} h_{FE3}	*DC Current Gain	V_{CE} = 1V, I_C = 0.1A V_{CE} = 1V, I_C = 2A V_{CE} = 1V, I_C = 5A	60 100 50		400	
V_{CE}(sat)	*Collector-Emitter Saturation Voltage	I_C = 2A, I_B = 0.2A		0.1	0.3	V
V_{BE}(sat)	*Base-Emitter Saturation Voltage	I_C = 2A, I_B = 0.2A		0.9	1.2	V
t_{ON}	Turn ON Time	V_{CC} = 10V, I_C = 2A		0.2	1	μs
t_{STG}	Storage Time	I_{B1} = - I_{B2} = 0.2A		1.1	2.5	μs
t_F	Fall Time	R_L = 5Ω		0.2	1	μs

* Pulse test: PW≤50μs, duty Cycle≤2% Pulsed

h_{FE} Classificntion

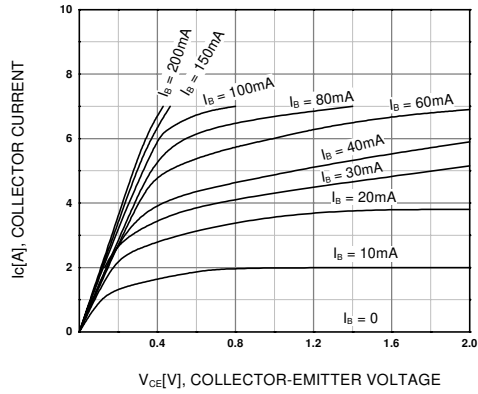| Classification	O	Y	G
$h_{FE\ 2}$	100 ~ 200	160 ~ 320	200 ~ 400

Typical Characteristics

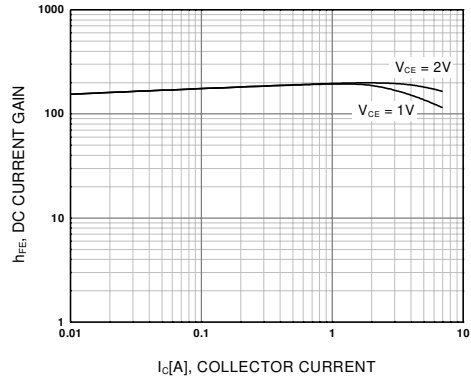**Figure 1. Static Characteristic**
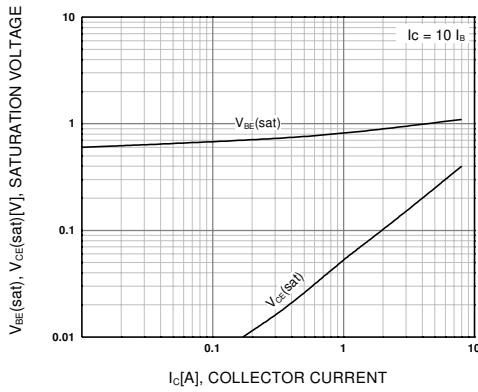

Figure 2. DC current Gain

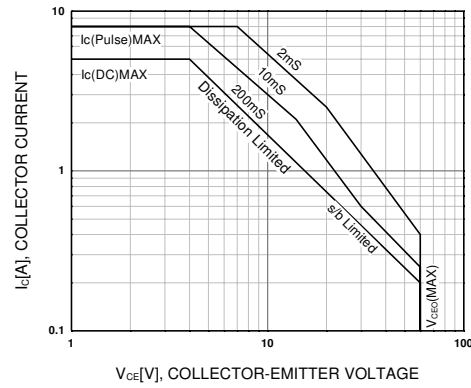**Figure 3. Collector-Emitter Saturation Voltage
Base-Emitter Saturation Voltage**
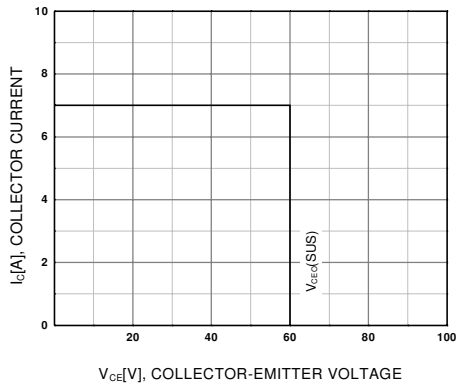

Figure 4. Forward Bias Safe Operating Area

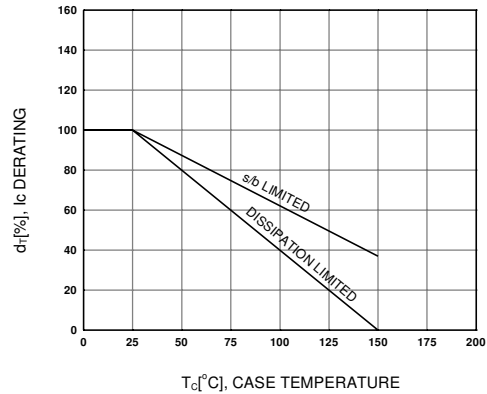**Figure 5. Reverse Bias Safe Operating Area**

Figure 6. Derating Curve of Safe Operating Areas
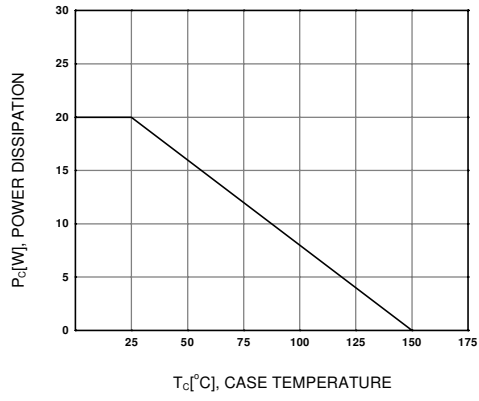
Typical Characteristics (Continued)

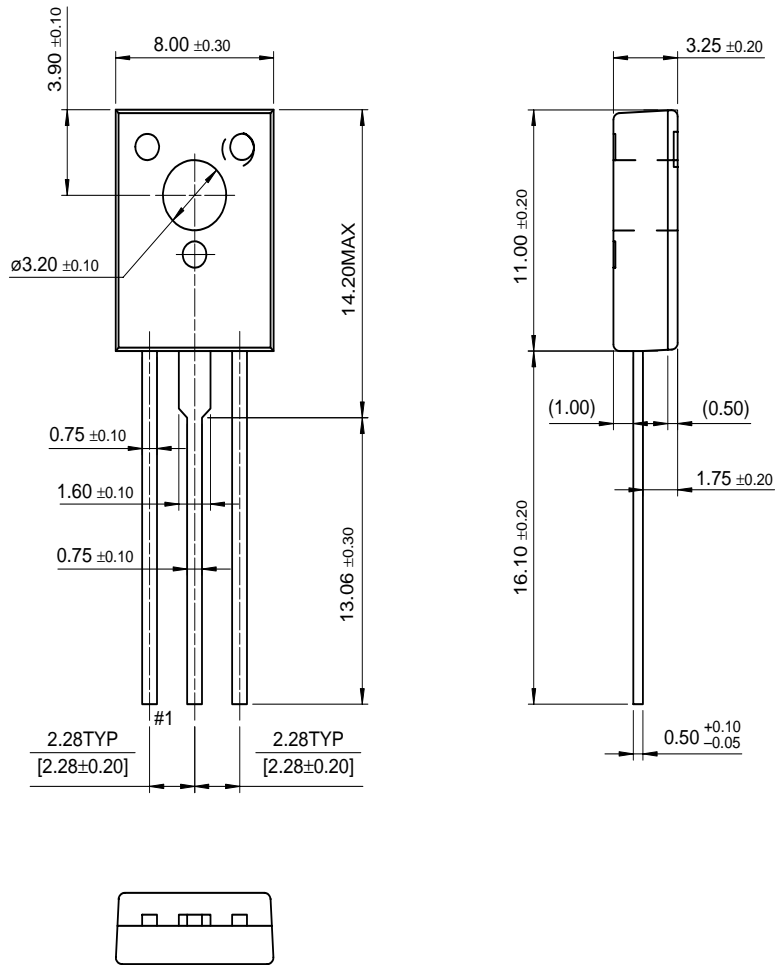**Figure 7. Power Derating**

X-axis: $T_C[°C]$, CASE TEMPERATURE
Y-axis: $P_C[W]$, POWER DISSIPATION

Package Demensions

TO-126

3.90 ±0.10

8.00 ±0.30

3.25 ±0.20

ø3.20 ±0.10

14.20MAX

11.00 ±0.20

0.75 ±0.10

1.60 ±0.10

0.75 ±0.10

(1.00)

(0.50)

1.75 ±0.20

13.06 ±0.30

16.10 ±0.20

#1

2.28TYP
[2.28±0.20]

2.28TYP
[2.28±0.20]

0.50 +0.10 −0.05

Dimensions in Millimeters

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx™	HiSeC™	SuperSOT™-8
Bottomless™	ISOPLANAR™	SyncFET™
CoolFET™	MICROWIRE™	TinyLogic™
CROSSVOLT™	POP™	UHC™
E^2CMOS™	PowerTrench®	VCX™
FACT™	QFET™	
FACT Quiet Series™	QS™	
FAST®	Quiet Series™	
FASTr™	SuperSOT™-3	
GTO™	SuperSOT™-6	

DISCLAIMER
FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR INTERNATIONAL.
As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

PUBLICATION ORDERING INFORMATION

© Semiconductor Components Industries, LLC   www.onsemi.com